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U.S. PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME		CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
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EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
OTHER ART, JOURNAL ARTICLES, ETC.									
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)								
DLN	C1	Campbell et al. "Multiplication Noise of Wide-Bandwidth InP/InGaAsP/InGaAs Avalanche Photodiodes." <i>J. Lightwave Technol.</i> , Vol. 7, No. 3, pp. 473-477, 1989.							
	C2	Campbell et al. "High-Speed InP/InGaAsP/InGaAs Avalanche Photodiodes Grown by Chemical Beam Epitaxy," <i>IEEE J. Quantum Electron.</i> , Vol. 24, No. 3, pp. 496-500, 1988.							
	C3	Watanabe et al. "High-Speed and Low-Dark-Current Flip-Chip InAlAs/InAlGaAs Quaternary Well Superlattice APD's with 120 GHz Gain-Bandwidth Product," <i>IEEE Photon. Tech. Lett.</i> , Vol. 5, No. 6, pp. 675-677, 1993.							
	C4	Forrest. "Performance of $\text{In}_x\text{Ga}_{1-x}\text{As}_y\text{P}_{1-y}$ Photodiodes with Dark Current Limited by Diffusion, Generation Recombination, and Tunneling" <i>IEEE J. Quantum Electron.</i> , Vol. QE-17, No. 2, February 1981.							
	C5	Tarof et al. "Planar InP/InGaAs Avalanche Photodetectors with Partial Charge Sheet in Device Periphery," <i>Appl. Phys. Lett.</i> , Vol. 57, No. 7, pp. 670-672, 1990.							
	C6	Ekholm et al. "High Bandwidth Planar InP/InGaAs Avalanche Photodiodes," <i>IEEE Trans. On Electron Dev.</i> , Vol. 35, No. 12, pp. 2434, 1988.							
DLN	C7	Bowers et al. "Chapter 17: High-Speed Photodetectors," <i>Handbook of Optics</i> , Vol. 1, McGraw-Hill, New York, 1995.							
EXAMINER		<i>Richard Nguyen</i>				DATE CONSIDERED		4/29/03	